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FDA59N30 N-Channel UniFETTM MOSFET 300 V, 59 A, 56 mΩ

Features

- $R_{DS(on)}$ = 47 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 29.5 A
- Low Gate Charge (Typ. 77 nC)
- Low C_{rss} (Typ. 80 pF)
- 100% Avalanche Tested

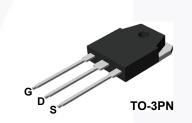
Applications

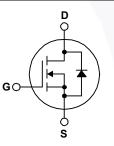
- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

May 2014

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter			FDA59N30	Unit	
V _{DSS}	Drain-Source Voltage			300	V	
ID	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)		59 35	A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	236	Α	
V _{GSS}	Gate-Source voltage			±30	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	1734	mJ	
I _{AR}	Avalanche Current		(Note 1) 59		А	
E _{AR}	Repetitive Avalanche Energy		(Note 1) 50		mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns	
P _D	Power Dissipation	(T _C = 25°C) - Derate Above 25°C		500 4	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

Thermal Characteristics

Symbol	Parameter	FDA59N30	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.25	°C/W
R_{\thetaJA}	Thermal Resistance, Junction-to-Ambient, Max.	40	C/VV

FDA59N30 — N-Channel UniFETTM MOSFET

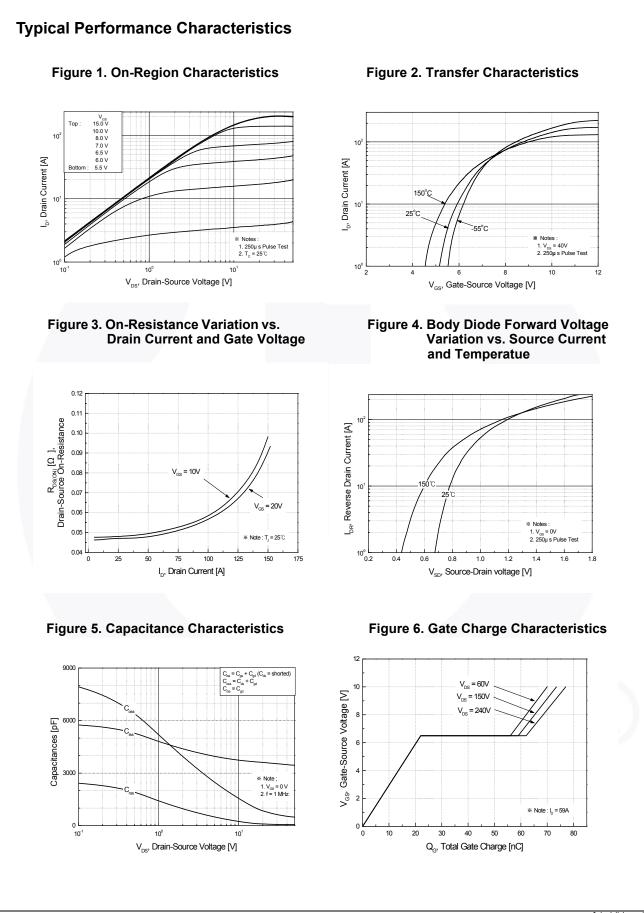
FDA59N30
— N-Channel
UniFET TM
MOSFET

Part N	Part Number Top Mark		Package	Packing Method	Reel Size	Та	pe Width	Qua	antity
		TO-3PN	• •		N/A		30 units		
Electric	al Char	racteristics T _c =	25°C unless	otherwise noted.					
Symbol		Parameter		Conditions		Min.	Тур.	Max.	Unit
Off Charac	teristics								
BV _{DSS}	Drain-Source Breakdown Voltage		V _{GS}	V _{GS} = 0 V, I _D = 250 μA		300			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient		I _D = 3	$I_D = 250 \ \mu$ A, Referenced to 25°C			0.3		V/°C
I _{DSS}	Zero Gate Voltage Drain Current			V_{DS} = 300 V, V_{GS} = 0 V V_{DS} = 240 V, T_{C} = 125°C				1 10	μΑ μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward		ward V _{GS}	V _{GS} = 30 V, V _{DS} = 0 V				100	nA
I _{GSSR}	Gate-Bod	ody Leakage Current, Reverse		V _{GS} = -30 V, V _{DS} = 0 V				-100	nA
On Charac	teristics								
V _{GS(th)}	Gate Thre	eshold Voltage	V _{DS}	= V _{GS} , I _D = 250 μA		3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance		V _{GS}	V _{GS} = 10 V, I _D = 29.5 A			0.047	0.056	Ω
9 _{FS}	Forward Transconductance		V _{DS}	V _{DS} = 40 V, I _D = 29.5 A			52		S
Dynamic C	haracteris	tics							
C _{iss}	Input Cap	acitance		V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz			3590	4670	pF
C _{oss}	Output Ca	apacitance	f = 1			\	710	920	pF
C _{rss}	Reverse 7	Fransfer Capacitance					80	120	pF
Switching	Characteri	stics							
t _{d(on)}	Turn-On [Delay Time		$V_{DD} = 150 \text{ V}, \text{ I}_{D} = 59 \text{ A},$ $V_{GS} = 10 \text{ V}, \text{ R}_{G} = 25 \Omega$ (Note 4)			140	290	ns
t _r	Turn-On F	Rise Time	V _{GS}				575	1160	ns
t _{d(off)}	Turn-Off	Delay Time					120	250	ns
t _f	Turn-Off F	all Time					200	410	ns
Qg	Total Gate	e Charge		V_{DS} = 240 V, I _D = 59 A, V _{GS} = 10 V (Note 4)			77	100	nC
Q _{gs}	Gate-Sou	rce Charge	V _{GS}				22		nC
Q _{gd}	Gate-Drai	n Charge					40		nC
Drain-Sou	rce Diode (Characteristics and Ma	ximum Ratii	ngs					
I _S	Maximum Continuous Drain-Source Diode Forward Current					59	Α		
I _{SM}	Maximum Pulsed Drain-Source Diode Fo			Current				236	Α
V _{SD}	Drain-Sou	rce Diode Forward Volt	age V _{GS}	= 0 V, I _S = 59 A				1.4	V
t _{rr}	Reverse F	Recovery Time	00	V _{GS} = 0 V, I _S = 59 A, dI _F /dt =100 A/µs			246		ns
Q _{rr}	Reverse F	Recovery Charge	dl _F /d				6.9		μC

Notes:

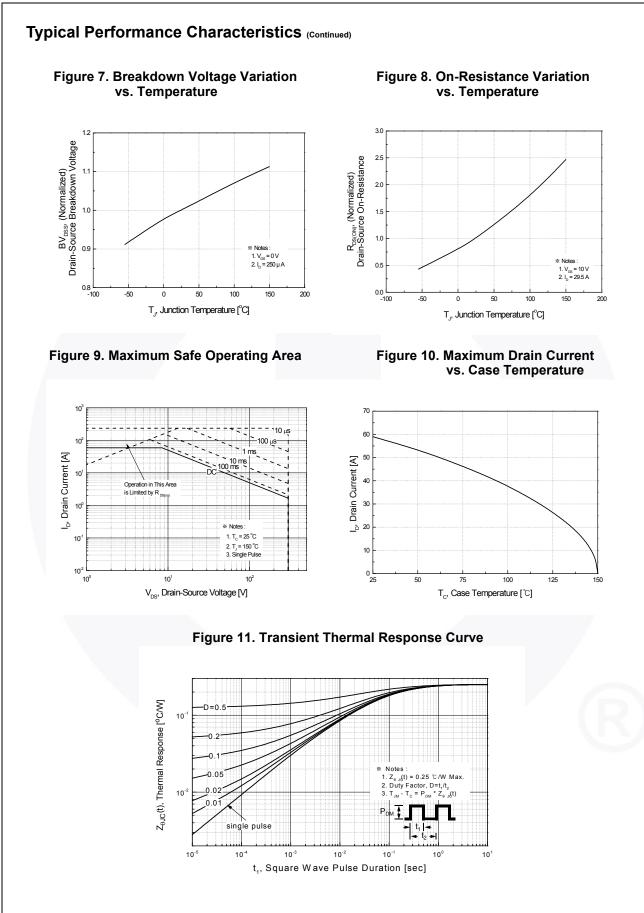
1. Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 0.83 mH, I_{AS} = 59 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C. 3. I_{SD} ≤ 59 A, di/dt ≤ 200 A/µs, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C. 4. Essentially independent of operating temperature typical characteristics.

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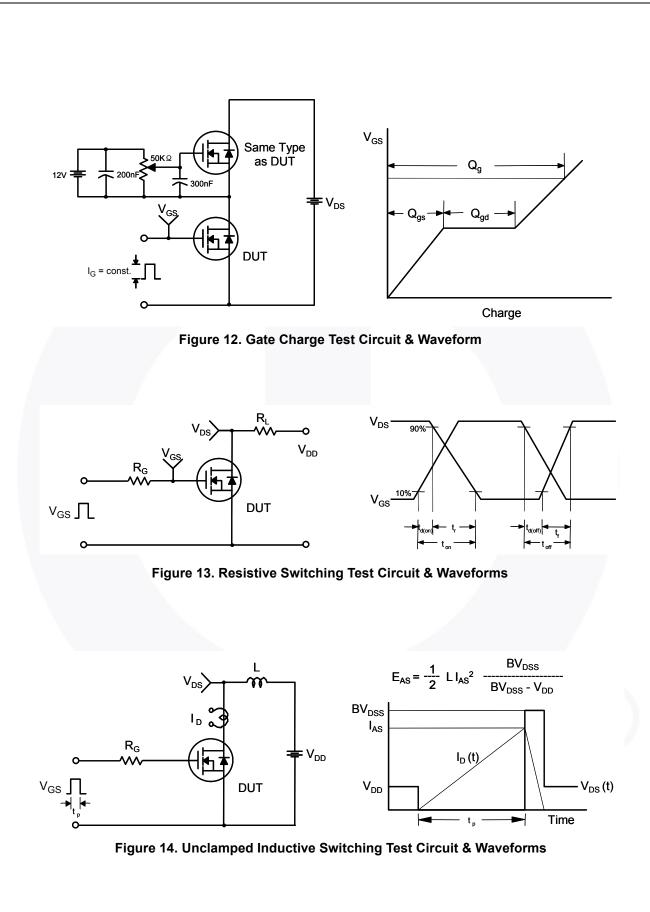


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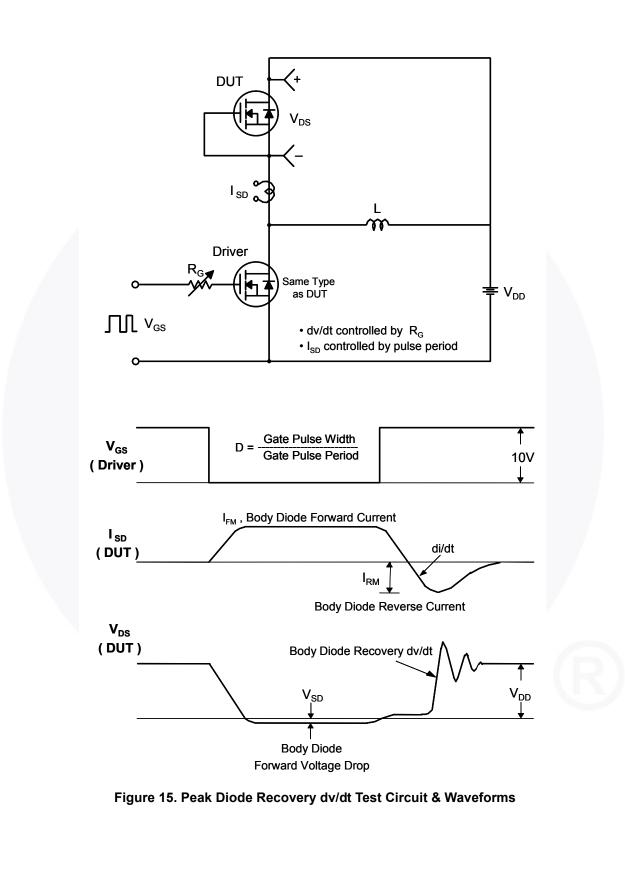
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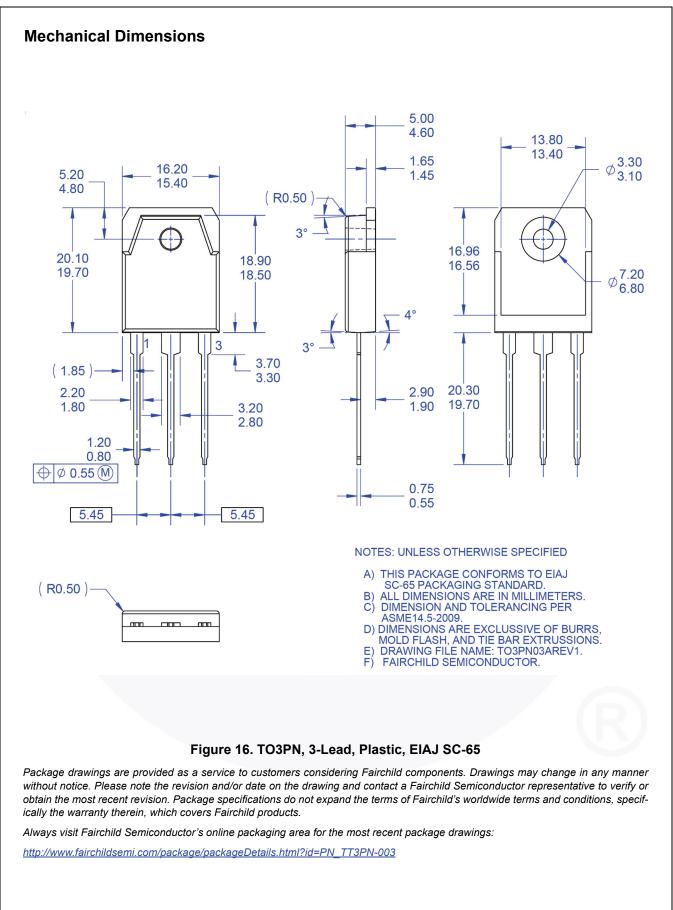


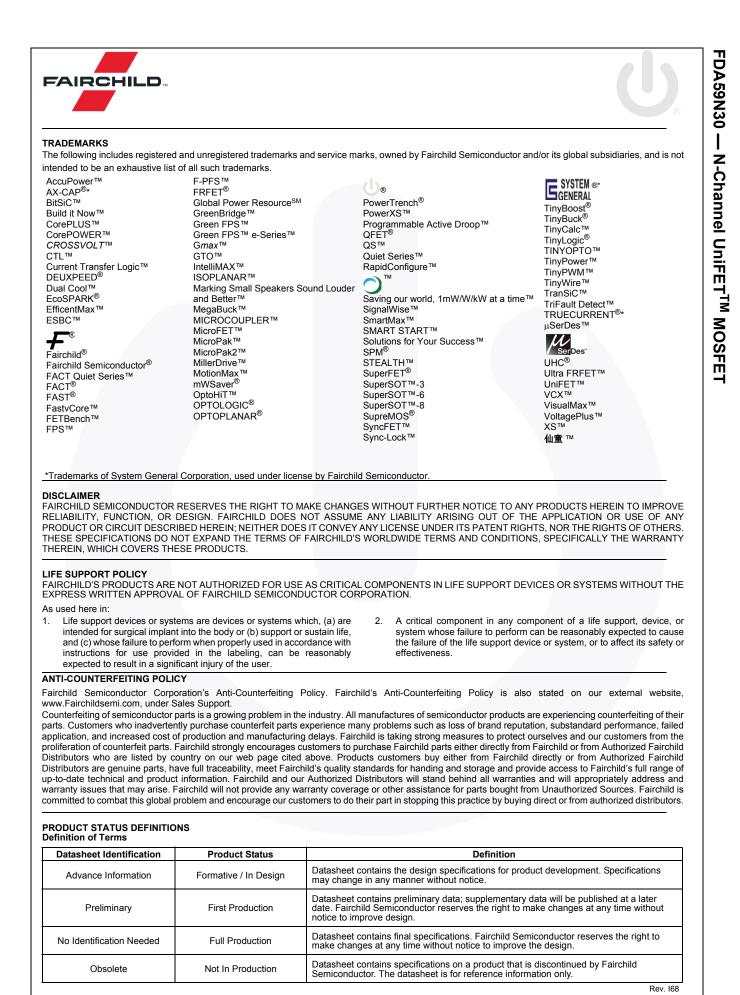
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